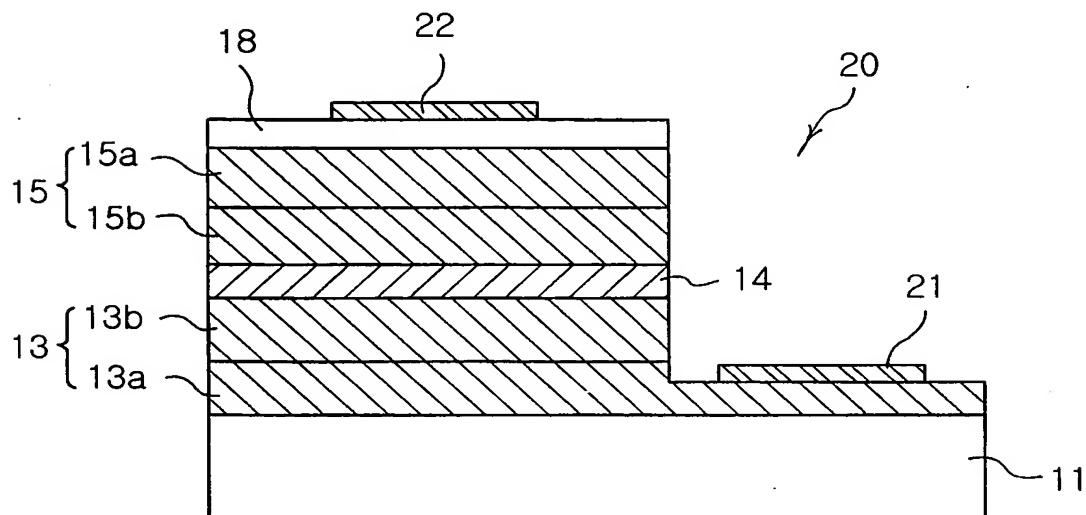


GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
METHOD FOR MANUFACTURING THE SAME

Inventor: Seung Wan CHAE

Docket No. 2336-257

1/5



PRIOR ART

FIG. 1

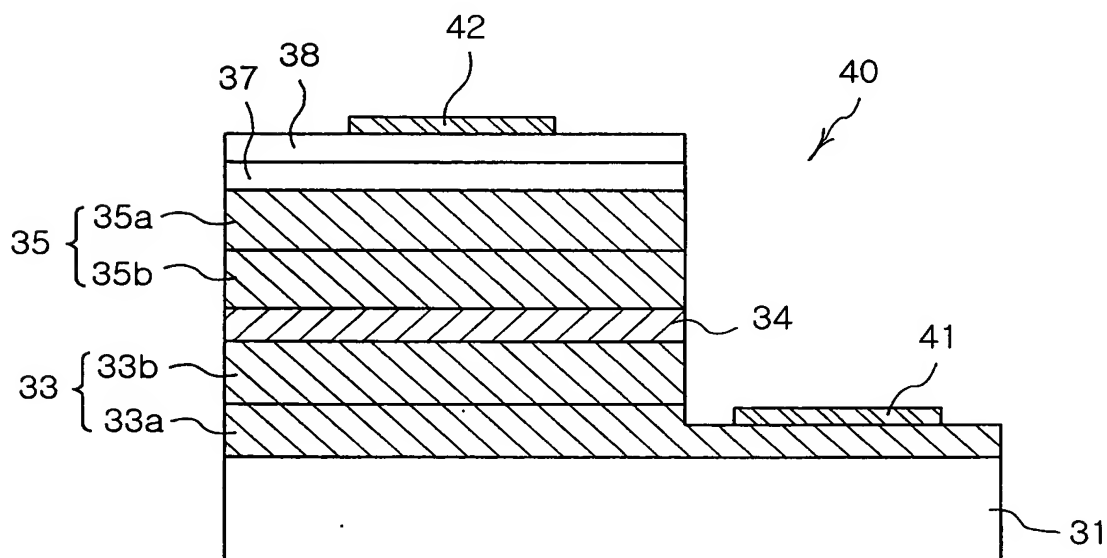


FIG. 2

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
METHOD FOR MANUFACTURING THE SAME

Inventor: Seung Wan CHAE

Docket No. 2336-257

2/5

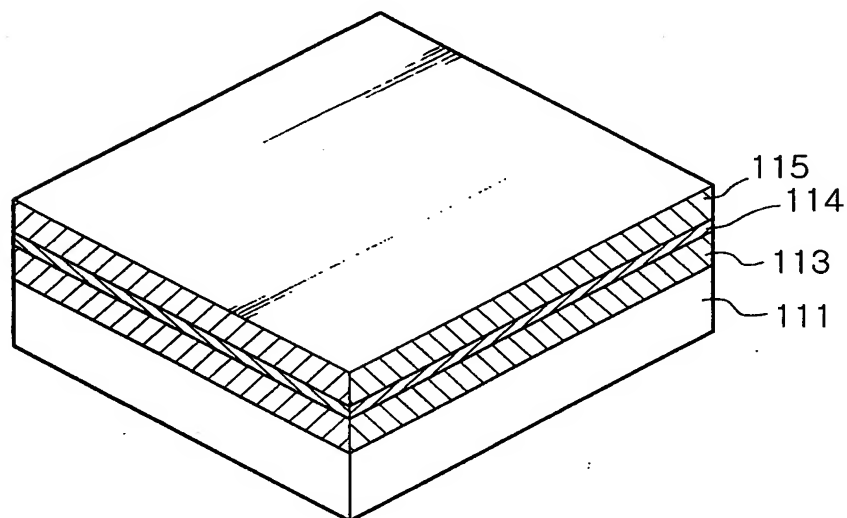


FIG. 3a

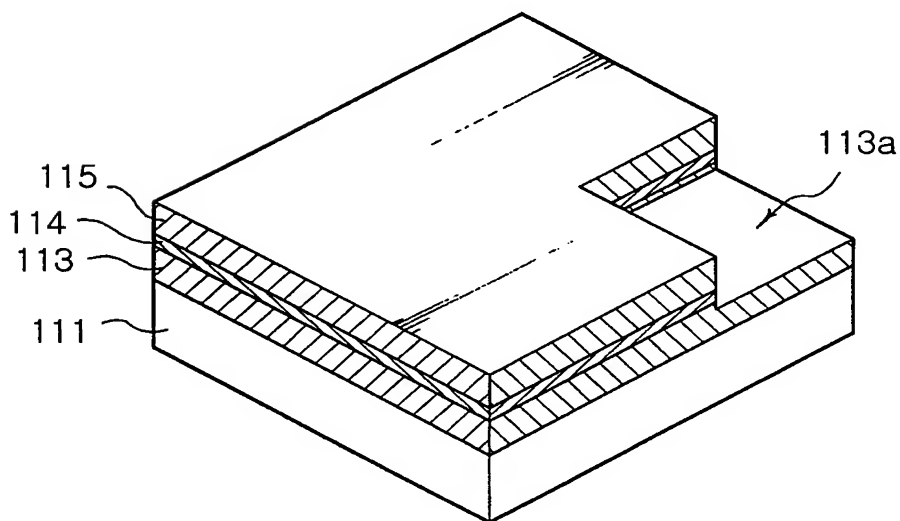


FIG. 3b

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
METHOD FOR MANUFACTURING THE SAME

Inventor: Seung Wan CHAE
Docket No. 2336-257

3/5

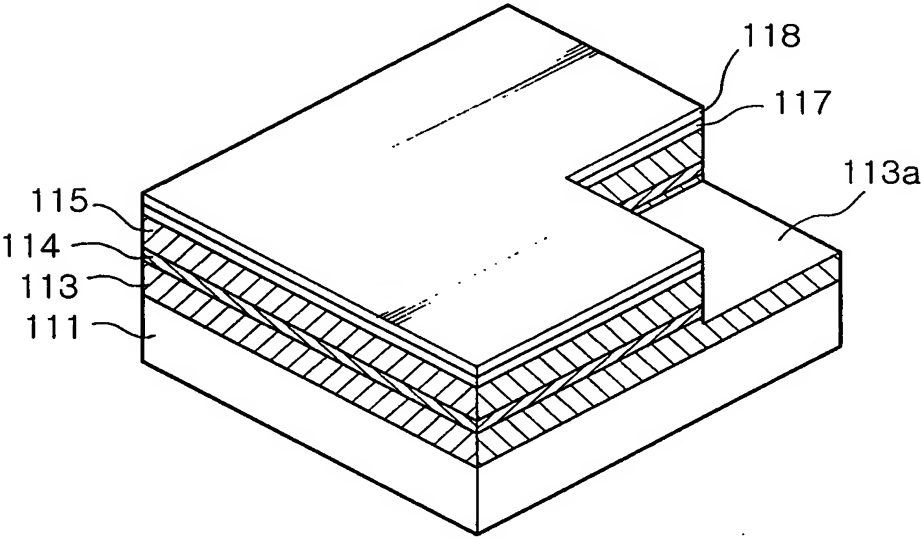


FIG. 3c

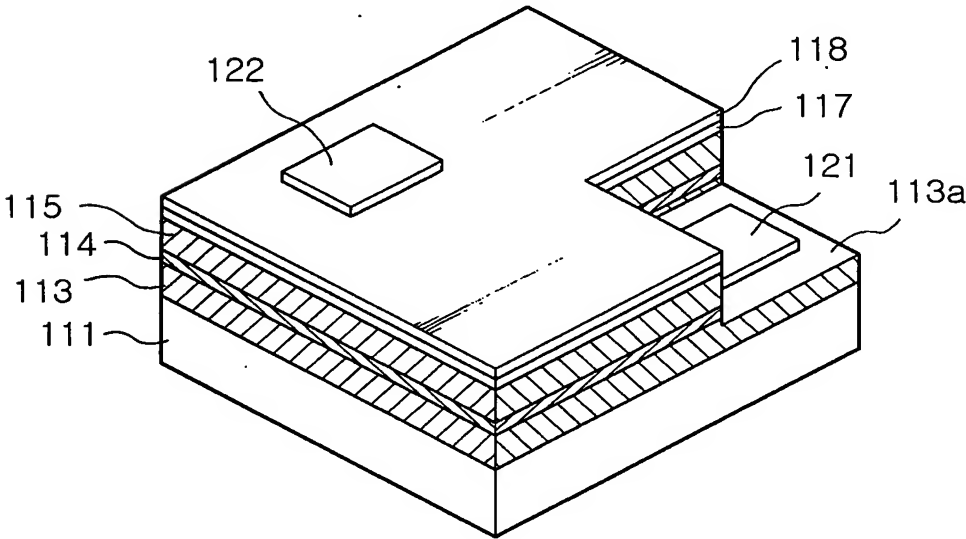


FIG. 3d

4/5

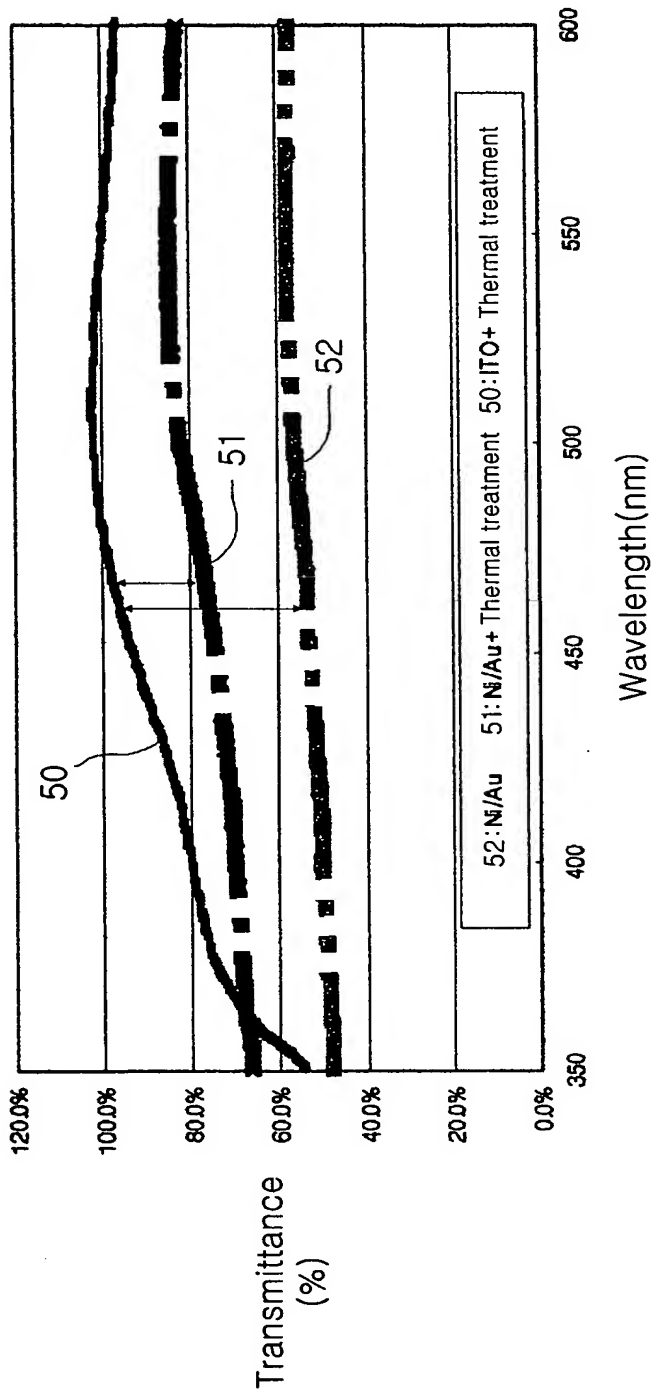


FIG. 4

GALLIUM NITRIDE (GaN)-BASED SEMICONDUCTOR LIGHT EMITTING DIODE AND
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Docket No. 2336-257

5/5

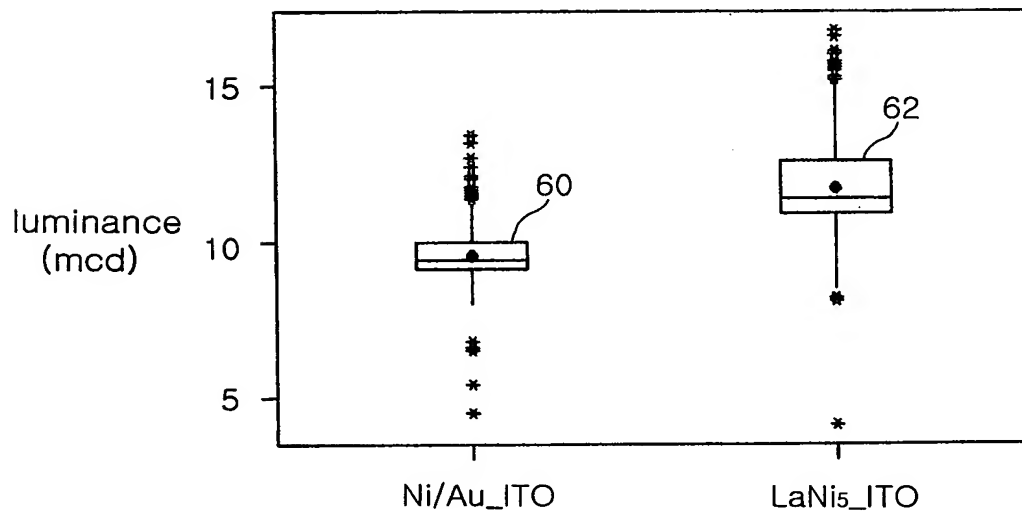


FIG. 5